



*EE141-Fall 2012
Digital Integrated
Circuits*

Lecture 2
Integrated Circuit Basics:
Manufacturing and Cost

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Last Lecture


- Last lecture
 - Introduction, Moore's law, future of ICs
- Today's lecture
 - Introduce basics of integrated circuit manufacturing and cost
- Reading: Ch 2.1, 2.2

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Administrative Stuff

- Discussions start this Friday
- Labs start next week
- Homework #1 is due this Thursday
 - Everyone should have an EECS instructional account
 - Use cory, quasar, pulsar

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*CMOS
Manufacturing
Process*

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HSPICE Syntax

Simple CMOS inverter

```
.include /home/ff/ee141/MODELS/gpdk090_mos.sp' TT_s1v

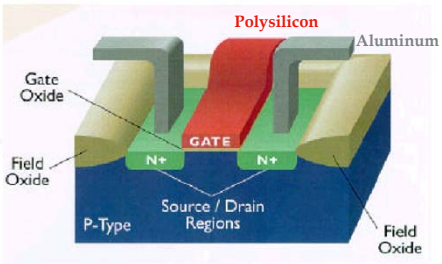
* netlist
Vdd vdd 0 1.2
VIN in 0 PULSE 0 1.2 200ps 100ps 100ps 2ns 4ns
M0 out in vdd vdd gpdk090_pmos1V L=100e-9 W=120e-9
M1 out in gnd gnd gpdk090_nmos1V L=100e-9 W=120e-9
R1 in gnd 10K
R2 out vdd 100K

* extra control information
.options post=2 nomod

* analysis
.op
.TRAN .01ns 3ns
.DC VIN 0 1.2 .001
.END
```

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The MOS Transistor



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The Manufacturing Process

For a complete walk-through of the process (64 steps), check the Book web-page

<http://bwrcc.eecs.berkeley.edu/lcBook>

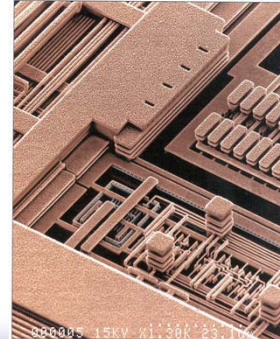
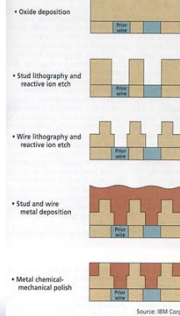
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Advanced Metallization

Dual damascene IC process

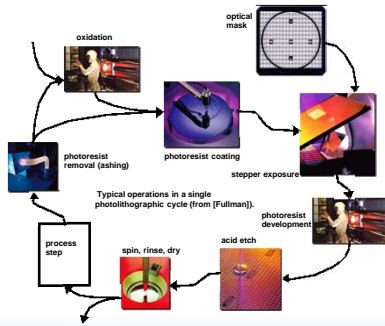


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Photo-Lithographic Process

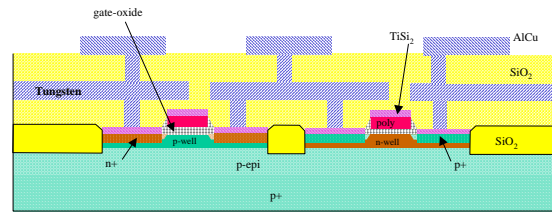


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A "Modern" CMOS Process



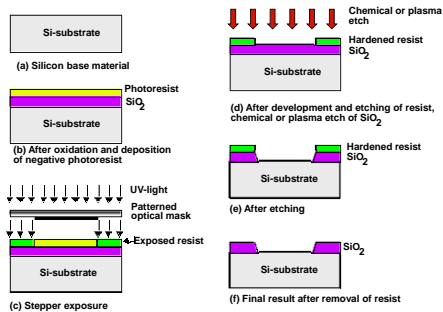
Dual-Well Shallow-Trench-Isolated CMOS Process

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Patterning of SiO₂



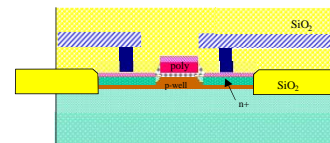
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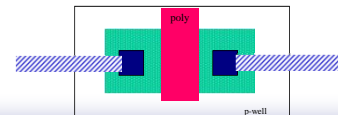
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Transistor Layout

Cross-Sectional View



Layout View



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Cost

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Total Cost

□ Cost per IC

$$\text{cost per IC} = \text{variable cost per IC} + \frac{\text{fixed cost}}{\text{volume}}$$

□ Variable cost

$$\text{variable cost} = \frac{\text{cost of die} + \text{cost of die test} + \text{cost of packaging}}{\text{final test yield}}$$

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Cost of Integrated Circuits

□ NRE (non-recurrent engineering) costs - fixed

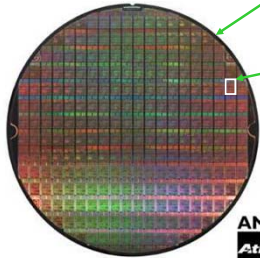
- Independent of volume (i.e., number of units made/sold)
- Examples: design time and effort, mask generation, equipment, etc.

□ Recurrent costs - variable

- proportional to volume
- Examples: silicon processing, packaging, test
- Most of these related to chip area


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Die Cost



Wafer

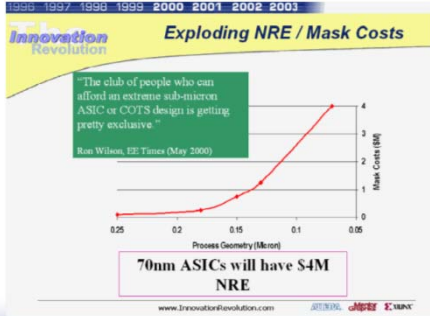
Single die

$$\text{cost of die} = \frac{\text{cost of wafer}}{\text{dies per wafer} * \text{die yield}}$$


From: <http://www.amd.com>

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NRE Cost is Increasing



Exploding NRE / Mask Costs

The club of people who can afford an extreme sub-micron ASIC or COTS design is getting pretty exclusive.

Ron Wilson, EE Times (May 2000)

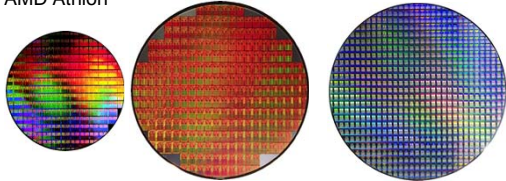
70nm ASICs will have \$4M NRE

www.innovationrevolution.com

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Wafer size

AMD Athlon



8" (200mm) 90nm CMOS

12" (300mm) 90nm CMOS

12" (300mm) 65nm CMOS

From: <http://www.sandpile.org>

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Yield

$$Y = \frac{\text{No. of good chips per wafer}}{\text{Total number of chips per wafer}} \times 100\%$$

$$\text{Die cost} = \frac{\text{Wafer cost}}{\text{Dies per wafer} \times \text{Die yield}}$$

$$\text{Dies per wafer} = \frac{\pi \times (\text{wafer diameter}/2)^2}{\text{die area}} = \frac{\pi \times \text{wafer diameter}}{\sqrt{2} \times \text{die area}}$$

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Next Lecture

- CMOS transistors as switches
- How to build an inverter
- Design metrics

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Defects

Yield = 1/4 Yield = 19/24

$$\text{die yield} = \left(1 + \frac{\text{defects per unit area} \times \text{die area}}{\alpha} \right)^{-\alpha}, \text{ where } \alpha \text{ is approximately } 3$$

$$\text{die cost} \propto \frac{1}{\left[(\text{die/wafer} \propto \text{die area}^{-1}) (\text{yield} \propto \text{die area}^{-3}) \right]} \propto \text{die area}^4$$

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